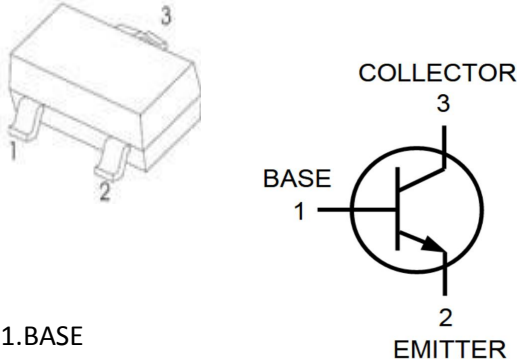
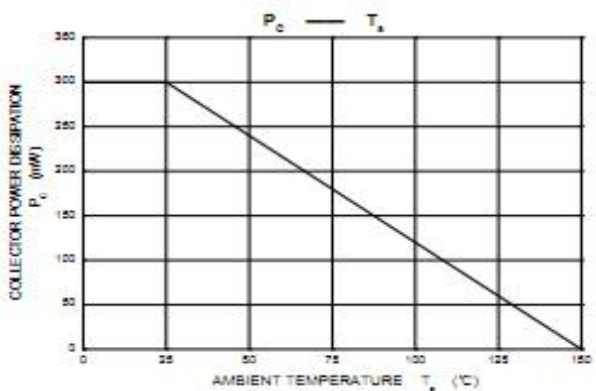
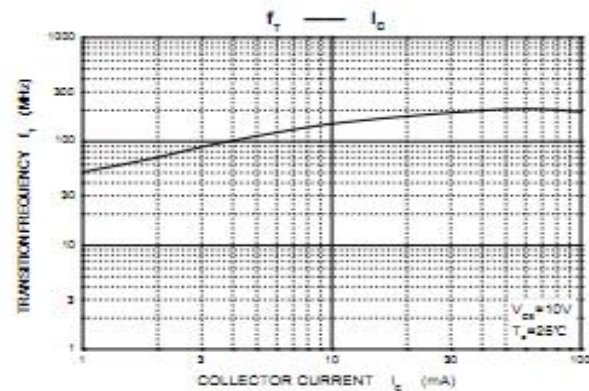
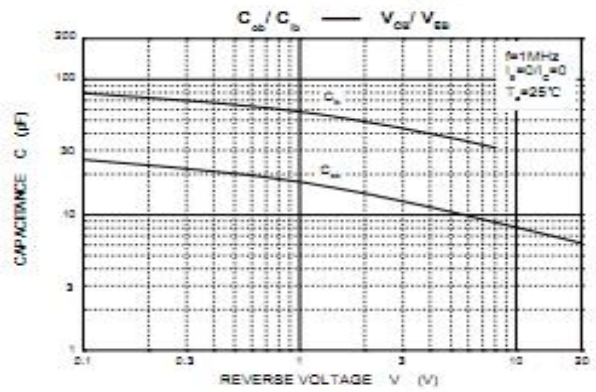
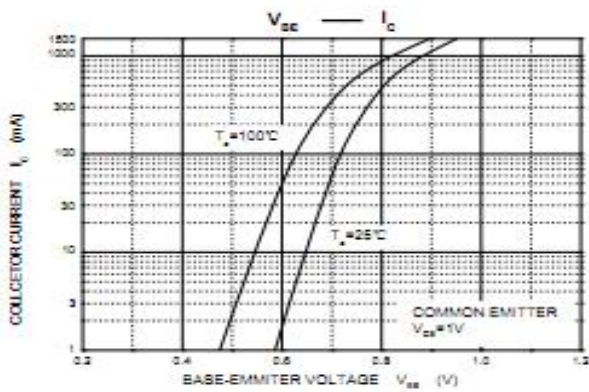
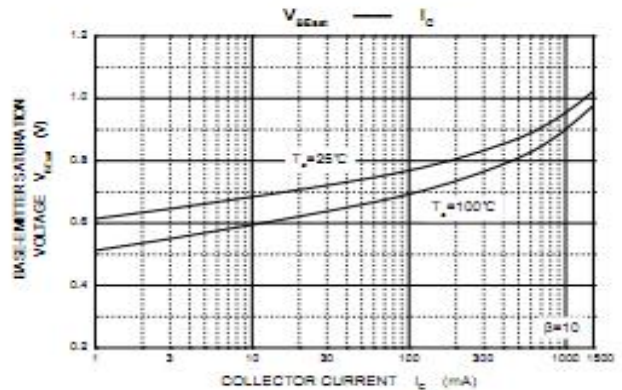
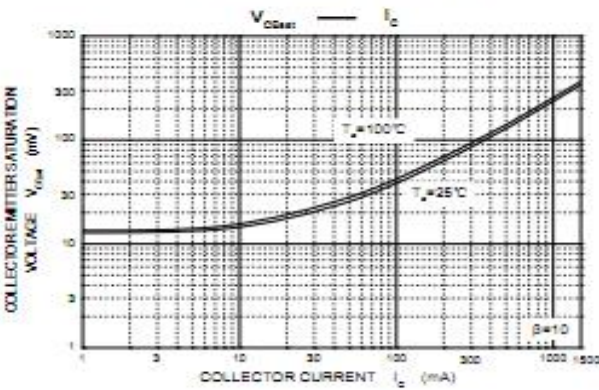
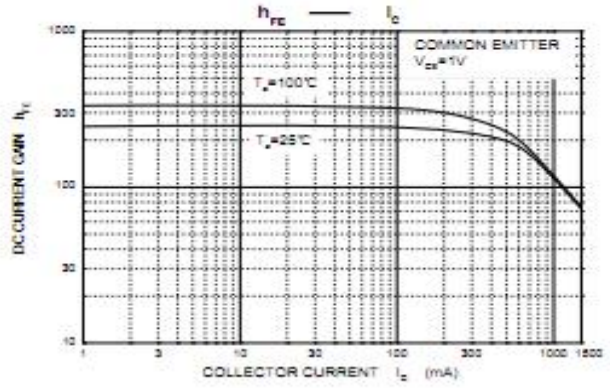
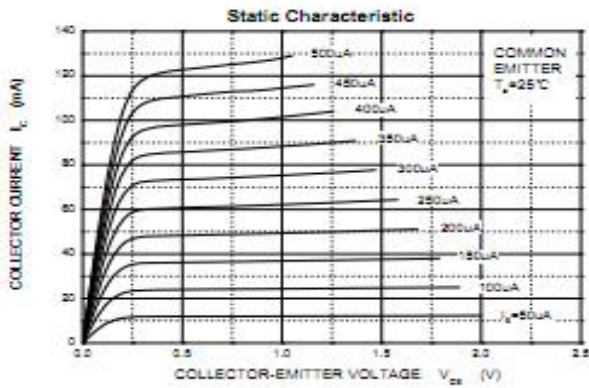


TRANSISTOR (NPN)		SOT-23 Plastic-Encapsulate Transistors	
<p><u>SOT-23</u></p>  <p>1. BASE 2. EMITTER 3. COLLECTOR</p> <p>Marking :Y1</p>		<p><b>Features</b></p> <ul style="list-style-type: none"> <li>※ Complimentary to SS8550</li> <li>※ Collector Current: <math>I_c=1.5A</math></li> </ul>	
<p><b>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</b></p>			
Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	40	V
Collector-Emitter Voltage	VCEO	25	V
Emitter-Base Voltage	VEBO	5	V
Collector Current	IC	1500	mA
Collector Power Dissipation	PC	300	mW
Thermal Resistance From Junction To Ambient	RθJA	417	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

<b>ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)</b>						
<b>Parameter</b>	<b>Symbol</b>	<b>Test Condition</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Unit</b>
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	40	100		V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	25	41		V
Emitter-base breakdown voltage	V(BR)EBO	IE=100μA, IC=0	5	8.6		V
Collector cut-off current	ICBO	VCB=40 V , IE=0			0.1	μA
Collector cut-off current	ICEO	VCB=25V , IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB= 5V , IC=0			0.1	μA
DC current gain	hFE	VCE=1V, IC= 50mA	120		400	
	hFE	VCE=1V, IC= 500mA	40			
Collector-emitter saturation voltage	VCE(sat)	IC=500 mA, IB= 50mA			0.6	V
Base-emitter saturation voltage	VBE(sat)	IC=500 mA, IB= 50mA			1.2	V
Transition frequency	fT	VCE=6V, IC= 20mA f=30MHz	150			MHz
<b>CLASSIFICATION OF hFI</b>						
<b>Rank</b>	<b>H</b>					
<b>Range</b>	<b>200-350</b>					

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)